

# Strain induced half-metal to semiconductor transition in GdN

Chun-gang Duan, R. F. Sabiryanov, Jianjun Liu, W. N. Mei

*Department of Physics, University of Nebraska at Omaha, Omaha, Nebraska 68182-0266*

P. A. Dowben, J. R. Hardy

*Department of Physics and Center for Materials Research and Analysis,  
University of Nebraska at Lincoln, Lincoln, Nebraska 68588*

(Dated: September 4, 2018)

## Abstract

We have investigated the electronic structure and magnetic properties of GdN as a function of unit cell volume. Based on the first-principles calculations of GdN, we observe that there is a transformation in conduction properties associated with the volume increase: first from half-metallic to semi-metallic, then ultimately to semiconducting. We show that applying stress can alter the carrier concentration as well as mobility of the holes and electrons in the majority spin channel. In addition, we found that the exchange parameters depend strongly on lattice constant, thus the Curie temperature of this system can be enhanced by applying stress or doping impurities.

PACS numbers: 75.10.-b, 71.27.+a, 71.70.Gm

Electronic and transport properties of the rare-earth nitrides have long been a challenge to investigators: the nitrides are difficult to fabricate into single phase crystals and the experimental picture of their electronic structures is far from clear. Although most rare-earth nitrides have shown to be semi-metallic, there are still uncertainties about GdN. Based on the direct resistivity measurements, Xiao *et al.* concluded that GdN is an insulator [1]. Nevertheless, the values they obtained for the resistivity do not rule out the possibility of a semi-metallic state. Furthermore, there is no clear-cut picture emerging from a series of studies by Kaldis and co-authors in 70's and 80's [2, 3, 4]. They pointed out that the specific resistivity decreased with increasing temperature, which suggests that the GdN system is semiconducting [2], while their later experiments on better quality samples showed a very large carrier concentration of  $1.9 \times 10^{21} \text{ cm}^{-3}$ , which is more characteristic of a semi-metal [3]. Even though the optical absorption edge for GdN is about 1 eV [4], which is similar to other rare-earth nitrides, at issue is the position of the chemical potential relative to the band edges in both the spin majority and spin minority band structures.

An appealing property of GdN is that it is ferromagnetic with a large gap at the Fermi energy in the minority spin states, according to the electronic structure calculations based on the local density approximation (LDA) [5, 6, 7]. At the same time GdN is semi-metallic in majority spin states with electron and hole pockets at the Fermi surface [6]. This latter property has led to some interest in GdN as a possible candidate for spin-dependent transport devices [8], exploiting the spin filter, giant magnetoresistance or tunneling magnetoresistance effects.

An accurate description of the electronic structure of rare-earth compounds is a very challenging problem because of their unfilled  $4f$  shells [9]. Calculations based on local spin density approximation (LSDA) are well known to underestimate the band gap in semiconductors. Thus LSDA and similar computational methods may not be able to correctly describe whether a highly correlated system, like GdN, is semi-metallic or semiconducting at the equilibrium volume [6]. Nonetheless, if we are interested in the trend of how the electronic and magnetic properties vary with the change of volume, we can obtain a reasonable picture for GdN from LSDA with additional Hubbard correlation terms describing on-site electron-electron repulsion associated with the  $4f$  narrow bands (LSDA+ $U$  approach) [10]. Actually, due to the fact that the  $f$  states of this system are exactly half occupied, there is no orbital moment and the anisotropic and multipole effects are minimal. As a result, GdN

is the ideal material to study the magnetic exchange interactions in rare-earth nitrides [11].

In this letter, we show that applying stress can influence significantly the electronic and magnetic properties of GdN. Using the first-principles approaches, we demonstrate that the system exhibits nominal “half-metallic” band structure at the equilibrium lattice constant, and then semi-metallic and/or semiconducting character develops with increasing lattice constant. We note that the magnetic properties are also extremely sensitive to the volume variations, i.e., the exchange interactions are at first ferromagnetic, then the calculated magnitudes of exchange parameters reduce substantially with increasing volume, suggesting that the Curie temperature is reduced with an increase in lattice constant.

The first-principles band structure approach applied in this work is the full-potential linear-augmented-plane-wave plus local-orbital method [12]. In the total energy calculations, the factor  $R_{MT}K_{max}$  is chosen to be 8. We found that using as large as 4000  $k$ -points in the Brillouin zone was necessary to obtain the energy convergence up to 0.1 meV. Following the previous work [13], we used a Hubbard  $U = 6.7$  eV and an exchange  $J = 0.7$  eV for Gd compounds in the LSDA+ $U$  scheme [10]. The calculated density of states (DOS) of GdN agrees well with photoemission data of nitrogen covered Gd(0001) surfaces [14], as shown in Fig. 1. Given that both experiment and theory share the similar lattice structures, this suggests that our computational approach correctly represents the electronic structure of GdN.

When we studied the band structure, we found that, for the theoretical lattice constant  $a = 4.92$  Å [Fig. 2(a)], our LSDA+ $U$  calculations show that there exist a hole pocket at  $\Gamma$  point and an electron pocket at X point. Strong hybridization between Gd 5*d* and N 2*p* spin majority states is clearly shown around the X point, while there is no such hybridization for spin minority states, indicating GdN to be half-metallic, with a gap about 0.6 eV in the spin minority channel. As we increase the lattice constant, this system gradually develops semi-metallic features in the majority states: e.g., the  $d - p$  hybridization around X point disappears and the Fermi level down shifts to the top of the hole section at  $\Gamma$  point [Fig. 2(b)]. With further increase of volume the system eventually becomes semiconducting [Fig. 2(c)]. The exact volume at which metal-semimetal or semimetal-semiconductor transitions occurs might not be precisely determined from LSDA-based calculations. However, the trend is clear and the predicted transitions could be observed experimentally.

We note that volume expansion or applied strain can be used to control the carrier density

as well as to some degree the mobility of the carriers, as can be seen from the band dispersion curves near the Fermi energy, in Fig. 2. At larger volumes the electron (hole) pockets become substantially shallower, meaning that the bottom (top) of the band approaches the Fermi energy and the area of the Fermi surface decreases. This is quite clear, for example, when comparing the hole pockets around  $\Gamma$  point in Fig. 2(a) and (b), especially those Fermi-level crossing points. As a result, the density of states at the Fermi energy reduces by about 50% when lattice parameter is increased by only 5%. And the decrease of  $dE_k/dk$  (tangent to the band dispersion) at Fermi level can also be seen from Fig. 2, indicating that the mobility of the holes decreases with the increase of the cell volume.

Furthermore, as also can be seen from Fig. 2, the indirect band gap of GdN can be modified by hydrostatic pressure. Based on the prediction of electron-hole-liquid theory [15], a first-order semiconductor to semimetal transition starts to take place as the indirect band gap decreases with decreasing lattice constant. Thus it is conceivable that with proper control of the indirect gap via external pressure, it is possible to explore the ground state of this correlated electron-hole liquid, and tune experimentally the semimetal phase transition.

We have also explored the modifications of the band structure and electronic properties due to the biaxial strain, which can be produced by epitaxially growing the film on the substrate with a different lattice constant. When the lattice parameter of the substrate is different from that of equilibrium GdN, the lattice mismatch can produce strain. In such cases, the lattice symmetry of GdN becomes tetragonal with  $c/a$  ratio less than 1 (larger substrate lattice constant, tensile strain) or larger than 1 (smaller substrate lattice constant, compressive strain). We performed total energy calculation on the Poisson ratio  $\nu$  for GdN by applying the biaxial strain in  $ab$  plane and observing the variation of  $c$ , then by comparing the biaxial strain given as

$$\frac{\Delta c/c_0}{\Delta a/a_0} = -\frac{2\nu}{1-\nu},$$

we deduced a  $\nu = 0.2$ , which is small compared to metals but similar to the known value of TiN. We found that the trend of band structure change, due to the biaxial strain, remains qualitatively the same as that caused by volume strain, which is expected because of the small Poisson ratio. The unit cell volume of GdN increases due to biaxial tensile stress, hence the modification of the band structure near the Fermi energy is similar to that observed during volume expansion. This may imply that the tensile stress tends to force the system to be less metallic and decreases the density of states near Fermi surface. When applying the

compressive strain, the system tends to become more metallic. Based on our calculations, the minority spin shows considerable reduction in the band gap with bands cross over Fermi energy with in-plane compressive strain of 3% and then the system is no longer half-metallic.

We also found that the change in electronic structure with the applied stress significantly affects the magnetic properties of GdN, particularly, the exchange interactions. We analyzed the exchange interactions using Heisenberg Hamiltonian:

$$H = - \sum_n J_n \sum_{i>j} \vec{S}_i \cdot \vec{S}_j,$$

where  $J_n$  are exchange parameters and  $n$  is the index of the nearest-neighbor shell. In these calculations, we limited our considerations to the third nearest neighbor interactions, i.e.,  $n$  runs from 1 to 3. The exchange parameters used in the model Hamiltonian, are obtained from the first-principles band structure calculations. To do this, we carried out total energy calculations on four different magnetic ordering configurations of the fcc structure. One is ferromagnetic (FM) ordering, and the other three are anti-ferromagnetic (AFM) orderings, as have been described in Ref. [16] and here for convenience are called AFM I, II and III, respectively. According to the model Hamiltonian, the total exchange energies per magnetic lattice site of the four magnetic orderings can be explicitly expressed as:

$$E_{FM} = E_0 + 6J_1 + 3J_2 + 12J_3,$$

$$E_{AFMI} = E_0 - 2J_1 + 3J_2 - 4J_3,$$

$$E_{AFMII} = E_0 - 3J_2,$$

$$E_{AFMIII} = E_0 - 2J_1 + J_2 + 4J_3,$$

where  $E_0$  is the reference energy. Based on these equations and the results obtained from the total energy calculations, those  $J$  parameters can be deduced accordingly. Due to the fact that the energy differences between these ordering states are generally very small, extreme care is needed in the calculations. Hence, comparisons are only made between FM and AFM energies calculated on the same structure and with the same computational parameters, to avoid any error caused by the different symmetries or shapes.

Our LSDA+ $U$  calculation gives the correct ground state for GdN, i.e., FM ordering. The  $J_n$  values are, nonetheless, quite small, which is expected from the low transition temperature. In addition, we found that these exchange parameters of GdN depend strongly on the

lattice constant (Fig. 3). When the lattice constant is increasing, the FM  $J_1$  decreases and  $J_2$  even changes sign, namely from FM to AFM, while  $J_3$  keeps almost the same. Thus the FM transition temperature  $T_c$ , which is proportional to the sum of neighboring exchange energies  $12J_1 + 6J_2 + 24J_3$  according the mean-field theory, is sensitive to the change of lattice constants.

It is well known that the oscillatory Rudermann-Kittel-Kasuya-Yosida-type interaction varies sensitively with the density of charge carriers. Thus, based on the above observations, we can see that the enhancement of the exchange interactions between neighboring magnetic sites, when the lattice constant decreases, is caused by the increase of the number of free charge carriers as the GdN system becomes more metallic. Actually, the strong lattice constants dependence of the  $J$  parameters of GdN is a manifestation of strong lattice constants dependence of its electronic structure, which lies between the metal and insulator phase. Furthermore, the trend of  $J_2$  with the increase of the volume implies the strengthening of an AFM superexchange interaction when the system becomes less metallic. This can be understood as a competition between the superexchange and indirect carrier mediated exchange interactions. Usually the former is roughly proportional to  $t^2/U$ , where  $t$  is the band energy or hopping integral, and does not change too strongly when the lattice parameter increases. Whereas the later, as we already discussed, would decrease with the increase of the lattice constant. Hence this reduction causes an overall increase in the antiferromagnetic coupling between second-nearest-neighbor Gd sites. Therefore we can see that the magnetic properties of Gd nitride are strongly related to their electronic properties. Based on these findings, we expect that GdN, in which a strong AFM and FM competition exists, could be AFM [4] or even more complicated structure such as spin-glass [17] when experiencing different stress.

Monte Carlo (MC) simulations, based on the model Heisenberg Hamiltonian with *ab initio* derived exchange parameters are used to obtain the Curie temperature. Same method has been applied successfully in the study of complex permanent magnetic materials [18]. The lattice studied in our MC simulation is a  $10a \times 10a \times 10a$  fcc cell (4000 spins) with periodic boundary conditions, where  $a$  is the lattice constant. At theoretical lattice parameter ( $a = 4.92 \text{ \AA}$ ) we find the Curie temperature to be about 38 K, agreed reasonably well with the experimentally observed 58 K. This agreement is quite impressive, considering the strong correlated nature of this system. One possible reason for the underestimate of  $T_c$  may arise

from neglecting the correlated hopping processes in one-electron picture, which are higher order processes proposed by Kasuya and Li to explain of ferromagnetic exchange in GdN [19]. In addition, we found that the energy levels of  $4f$  states are crucial in determining the accurate exchange parameters. Our calculation on equilibrium structure of GdN, based on the present  $U$  parameter, gives the unoccupied  $4f$  states 5 eV above  $E_F$  and occupied  $4f$  states 6 eV below, which is in good qualitative agreement with the experimental situation [20], providing support for the validity of our studies of the magnetic properties of GdN.

Ordinarily, we would expect the ferromagnetic ground state to provide a stabilizing role to the spin-dependent electric conduction. Thus to enhance the Curie temperature of GdN to practical range is quite important. As we already mentioned above, one possible way is to apply stress. Moreover, doping impurities can also be an alternative: it was reported that by adding few percent of magnetic ions such as Mn, the  $T_c$  of GaN or ZnO well exceeds room temperature range [21], hence we believe this is a promising remedy for concern that the Curie temperature of GdN is on the low side.

In summary, we have found that there is a large lattice constant dependence of the electronic and magnetic properties in the spin dependent band structure of GdN. This material, with half-metallic gap about 0.6 eV, exhibits a ferromagnetic ground state, rendering it an attractive candidate for spintronic devices. Hence we appeal strongly for experimental efforts to study this interesting compound and validate our claim.

The authors acknowledge helpful discussions with A.G. Petukhov. This work was supported by the Office of Naval Research, Nebraska Research Initiative, the Nebraska-EPSCoR-NSF Grant EPS-9720643 and Department of the Army Grants DAAG 55-98-1-0273 and DAAG 55-99-1-0106. Computation work was completed utilizing the Research Computing Facility of the University of Nebraska – Lincoln.

---

[\*] Email address: dcg@cosmos.unomaha.edu.

[1] J.Q. Xiao, and C.L. Chien, Phys. Rev. Lett. **76**, 1727 (1996).

[2] G. Busch, E. Kaldis, E. Schaufelberger-Teker, P. Wachter, in Coll. Int. CNRS No. 180, Vol. I (CNRS, Paris-Grenoble 1970), p. 359.

[3] E. Kaldis and C.Zurcher, Helv. Phys. Acta **47**, 421 (1974).

- [4] P. Wachter and E. Kaldis, Solid State Commun. **34**, 241 (1980).
- [5] A. Hasegawa and A. Yanase, J. Phys. Soc. Jpn. **42**, 492 (1977).
- [6] A.G. Petukhov, W.R.L. Lambrecht, and B. Segall, Phys. Rev. B **53**, 3646 (1996).
- [7] Walter R. L. Lambrecht, Phys. Rev. B **62**, 13538 (2000).
- [8] S.A. Wolf, D.D. Awschalom, R.A. Buhrman, J.M. Daughton, S. von Molnar, M.L. Roukes, A.Y. Chtchelkanova, and D.M. Treger, Science **294**, 1488 (2001).
- [9] I. N. Yakovkin, Takashi Komesu, and P. A. Dowben, Phys. Rev. B **66**, 035406 (2002).
- [10] V.I. Anisimov, I.V. Solovyev, M.A. Korotin, M.T. Czyzyk, and G.A. Sawatzky, Phys. Rev. B **48**, 16929 (1993); V.I. Anisimov, J. Zaanen, and O.K. Andersen, *ibid.* **44**, 943 (1991).
- [11] D.X. Li, Y. Haga, H. Shida, T. Suzuki, Y.S. Kwon and G. Kido, J. Phys.: Cond. Matt. **9**, 10777 (1997).
- [12] P. Blaha *et al.*, Comput. Phys. Commun. **147**, 71 (2002).
- [13] Ph Kurz, G Bihlmayer and S Blügel, J. Phys.: Cond. Matt. **14**, 6353 (2002).
- [14] C. Waldfried, D.N. McIlroy, Dongqi Li, J. Pearson, S.D. Bader, and P.A. Dowben, Surf. Sci. **341**, L1072 (1995).
- [15] R. Monnier, J. Rhyner, T.M. Rice, and D.D. Koelling, Phys. Rev. B **31**, R5554 (1985).
- [16] J. Samuel Smart, *Effective field theories of magnetism* (W. B. Saunders Company, Philadelphia & London, 1966), p. 76-77.
- [17] D.X Li, K. Sumiyama and K. Suzuki, T Suzuki, Phys. Rev. **55**, 6467 (1997).
- [18] R.F. Sabiryanov and S.S. Jaswal, Phys. Rev. Lett. **79**, 155 (1997).
- [19] T. Kasuya and D.X. Li, J. Magn. Magn. Mater. **167**, L1 (1997).
- [20] H. Yamada, T. Fukawa, T. Muro, Y. Tanaka, S. Imada, S. Suga, D.-X. Li, and T. Suzuki, J. Phys. Soc. Jpn. **65**, 1000 (1996).
- [21] J.M. Coey, M. Venkatesan and C.B. Fitzgerald, Nature Materials **4**, 173 (2005).

FIG. 1: Comparison between the calculated DOS (majority spin: solid line, minority spin: dotted line) at theoretical lattice constant ( $a = 4.92 \text{ \AA}$ ) and the photoemission spectra for nitrogen on Gd(0001). The new photoemission features that are not attributable to the Gd(0001) substrate compare well with the calculated DOS for GdN. Features with strong N  $2p$  weight are indicated. Binding energies for experiment are shifted to higher binding energies as expected with a final state spectroscopy of a correlated electron system, but the shift is roughly uniform for key features of the photoemission spectra (taken for both  $s$  and  $p$  polarized light).

FIG. 2: Band structure of GdN in the vicinity of the Fermi energy for three volumes: (a) at the calculated equilibrium lattice parameter  $a = 4.92 \text{ \AA}$ , (b) at the lattice parameter increased by 5% ( $a = 5.16 \text{ \AA}$ ), (c) at the lattice parameter increased by 14% ( $a = 5.63 \text{ \AA}$ ). Solid and dotted lines represent spin majority and spin minority states, respectively. The change of conducting properties are indicated by the change of energy difference between the top (bottom) of the hole (electron) pockets and the Fermi energy.

FIG. 3: Exchange parameters of GdN plotted as function of the lattice constant; notice the strong volume dependence of  $J_1$  and  $J_2$ .